

isc Silicon NPN Power Transistor

ISCM18115

DESCRIPTION

- High Voltage Capability
- High Current Capability
- Fast Switching Speed

APPLICATIONS

Designed for high-voltage,high-speed, power switching in inductive circuits where fall time is critical. They are particularly suited for line-operated switchmode applications such as:

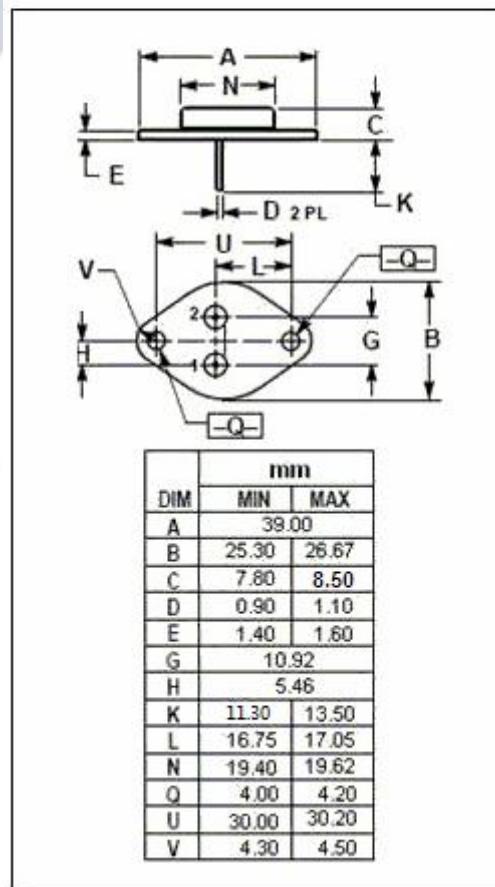
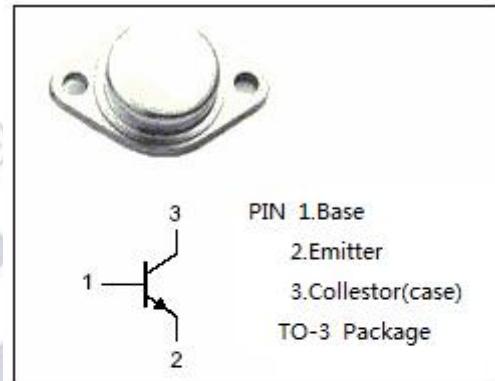
- Switching regulators
- Inverters
- Solenoid and relay drivers
- Motor controls
- Deflection circuits

Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	1200	V
V _{CEO}	Collector-Emitter Voltage	600	V
V _{EBO}	Emitter-Base Voltage	7	V
I _C	Collector Current-Continuous	15	A
I _{CM}	Collector Current-Peak	25	A
I _B	Base Current-Continuous	5	A
I _{BM}	Base Current-peak	10	A
P _C	Collector Power Dissipation @T _C =25°C	150	W
T _J	Junction Temperature	200	°C
T _{stg}	Storage Temperature Range	-65~200	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance,Junction to Case	1.0	°C/W



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ELECTRICAL CHARACTERISTICS
 $T_c=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(\text{SUS})}$	Collector-Emitter Sustaining Voltage	$I_C = 10\text{mA} ; I_B = 0$	600		V
$V_{(\text{BR})EBO}$	Emitter-Base Breakdown Voltage	$I_E = 5\text{mA} ; I_C = 0$	7		V
$V_{CE(\text{sat})-1}$	Collector-Emitter Saturation Voltage	$I_C = 8\text{A} ; I_B = 1.6\text{A}$		1.5	V
$V_{BE(\text{sat})}$	Base-Emitter Saturation Voltage	$I_C = 8\text{A} ; I_B = 1.6\text{A}$		1.6	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=1200\text{V} ; I_E = 0$		0.1	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V} ; I_C = 0$		0.1	mA
h_{FE}	DC Current Gain	$I_C = 5\text{A} ; V_{CE} = 5\text{V}$	10		

The Safe Operating Area figures
